



Estimated Gradient Limitation Insights for Different Surface Processing from Klystron Measurements

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TTC Meeting, July 2016



- Klystron testing overview
- N-doped niobium
- 120°C-baked niobium
- Nb₃Sn



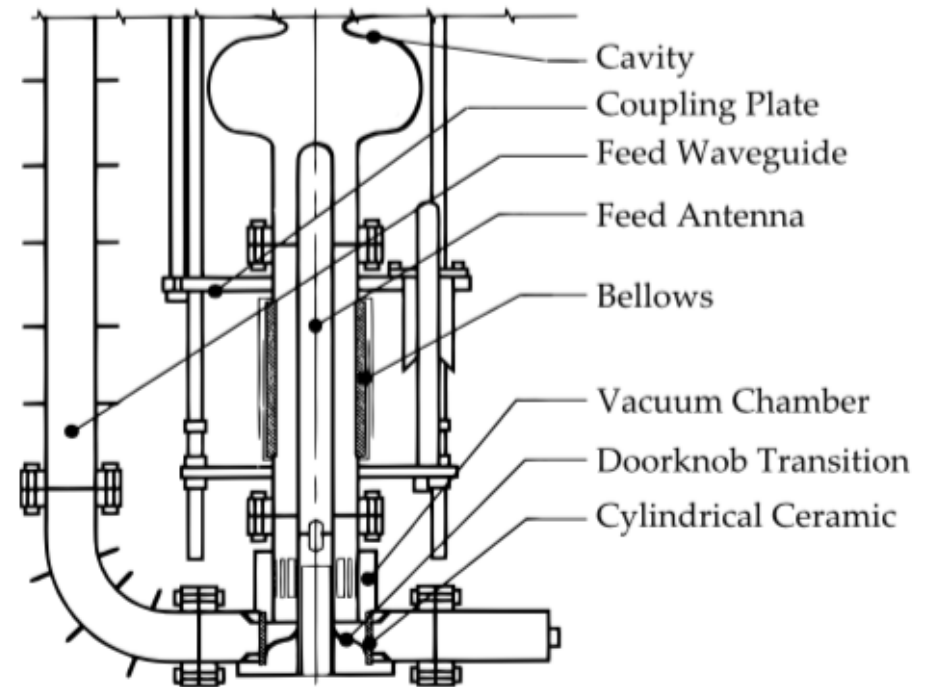
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- Klystron testing – motivation:
 - Escape global thermal effects by filling and quenching the cavity extremely quickly
 - Still limited by local effects
 - Probe higher fields than CW quench field
 - Probe fundamental fields in some cases (when heating not too strong)



- Klystron testing – apparatus



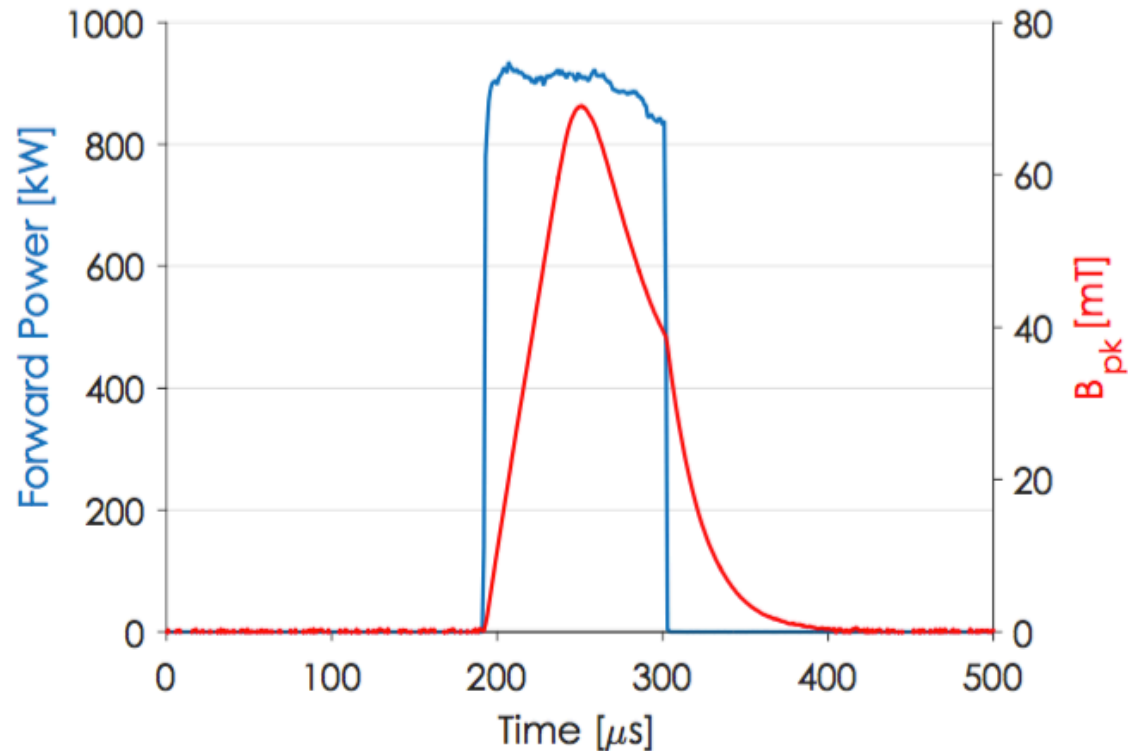


- Klystron testing – procedure
 - Typically preceded by CW test to calculate material properties
 - F vs. $T \rightarrow \lambda$ vs. T, ℓ, T_c
 - Q_0 vs. $T \rightarrow R_0, \Delta$
 - Q_0 vs. $E \rightarrow R_{BCS}$ vs. E
 - Pulsed testing:
 - Short (~ 100 us) pulses, up to 1 MW each P_f
 - Very strong coupling: $Q_{\text{ext}} \sim 10^6$



- Klystron testing – typical pulse

- P_f, P_r, P_t
- Quench field
 - Not necessarily the peak!
- Time to quench
- $Q(t)$



- Reminder:
 - $Q \propto U/P_{diss}$



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- N-doped cavities

- LTE1-2

- 900°C N-doping + 18 μm VEP
- Mean free path = 6 nm
- $B_{c1} = 37 \pm 8$ mT, $B_{sh} = 186 \pm 2$ mT
- CW quench field = 64 ± 4 mT

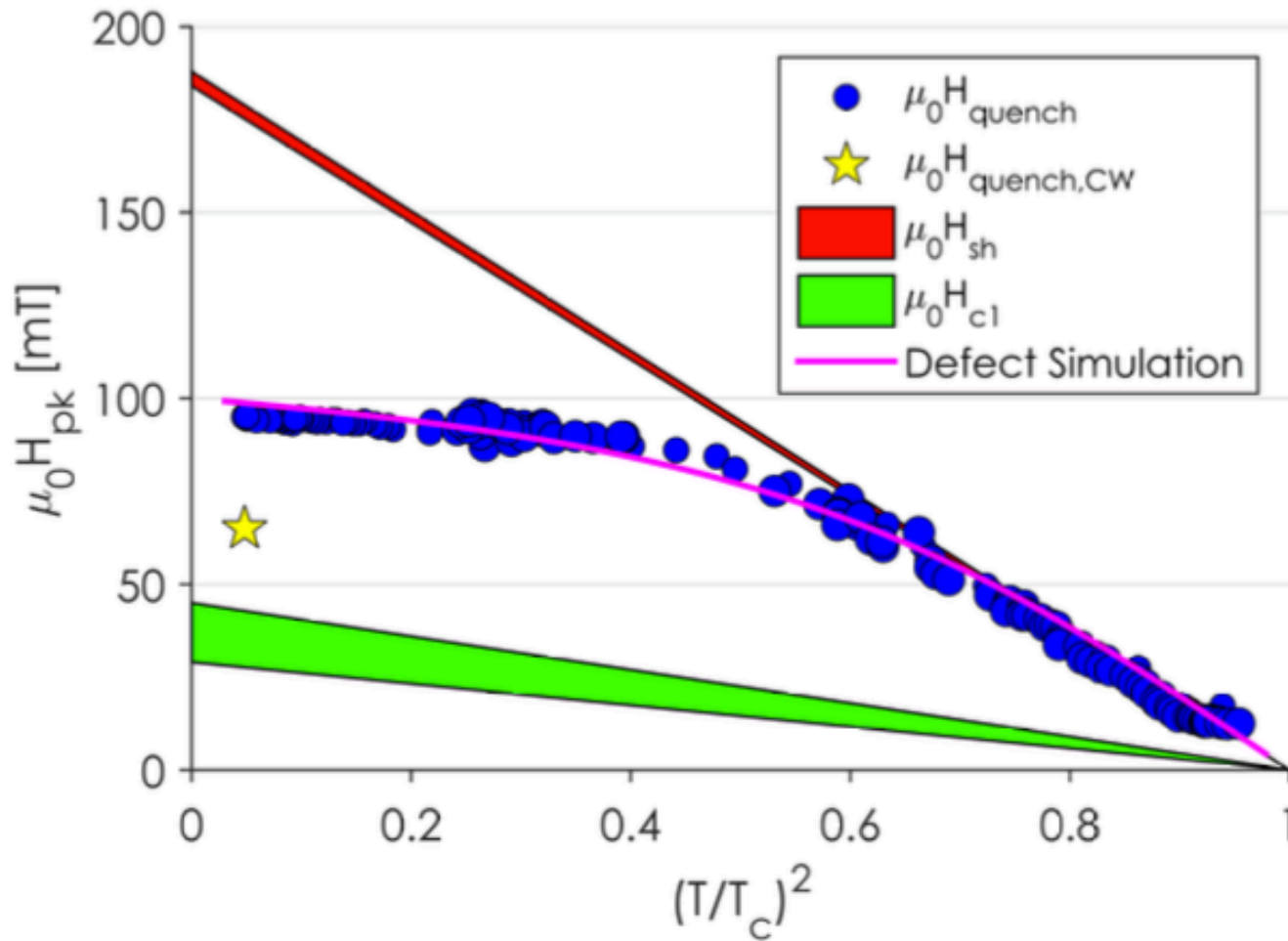
NB: Critical fields are given
at $T=0$

- LTE1-3

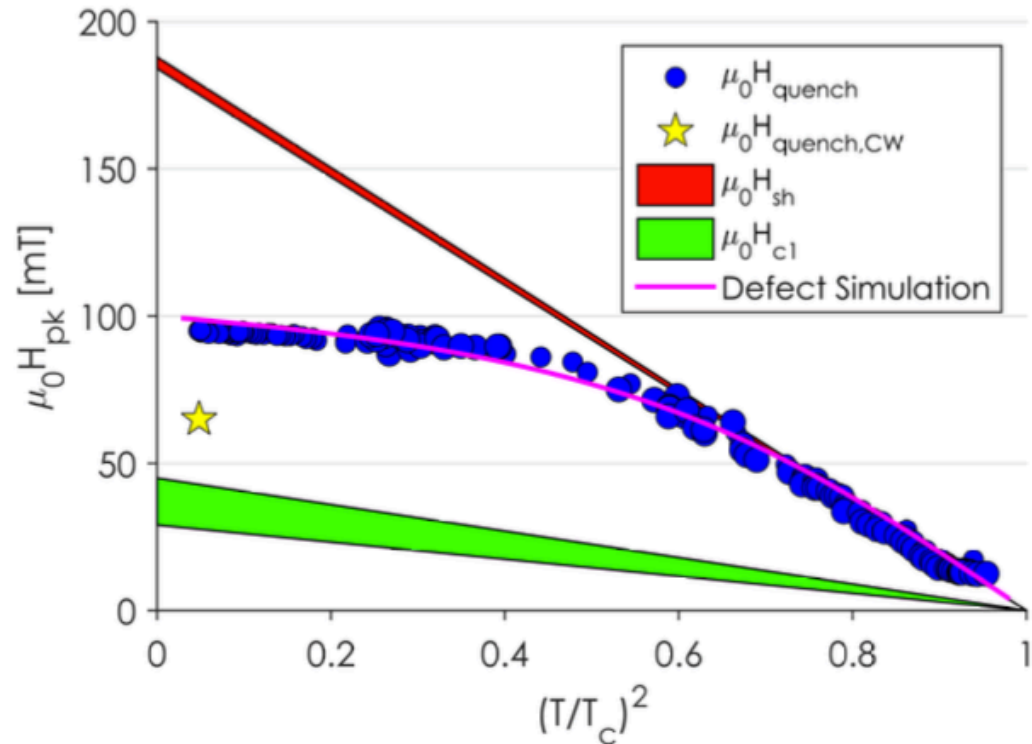
- 990°C N-doping + 5 μm VEP
- Mean free path = 4 nm
- $B_{c1} = 26 \pm 9$ mT, $B_{sh} = 179 \pm 3$ mT
- CW quench field = 40 ± 2 mT

Critical fields lowered
(B_{c1} strongly, B_{sh} somewhat)
in doped niobium

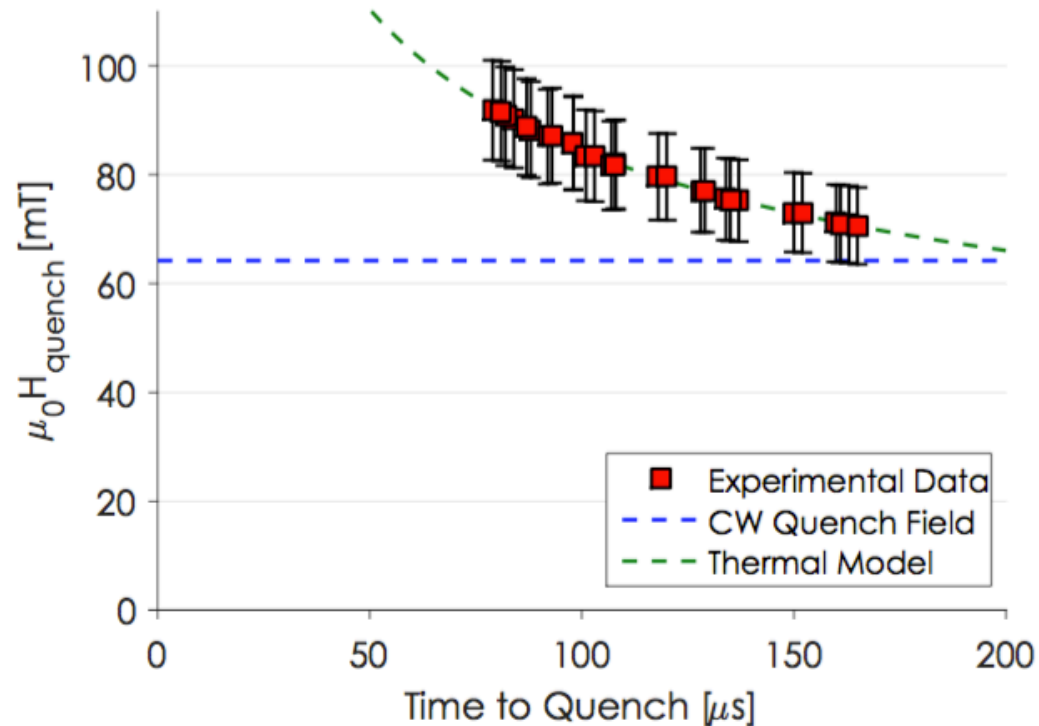
- LTE1-2 N-doped results



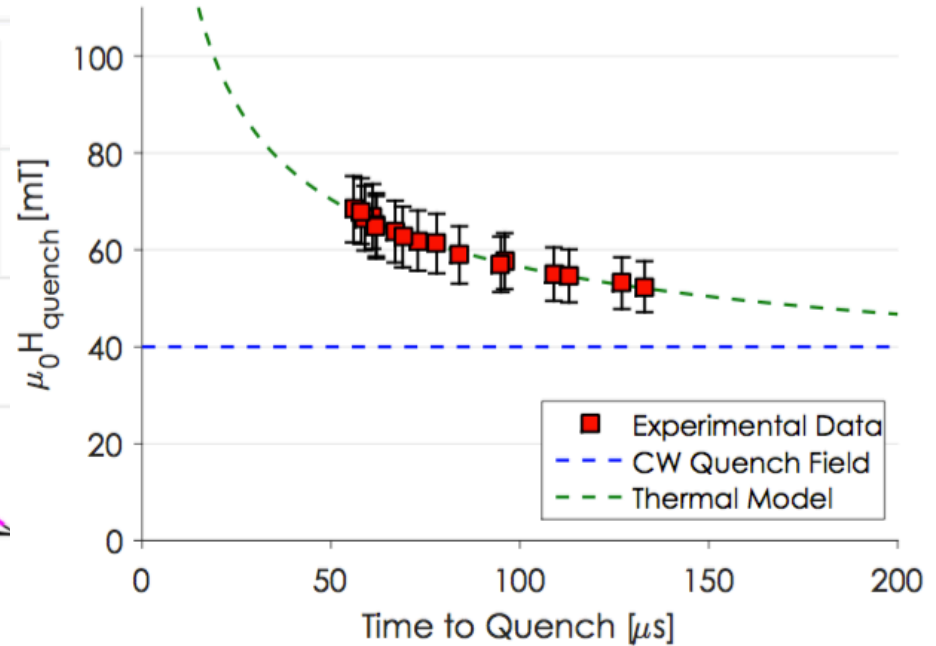
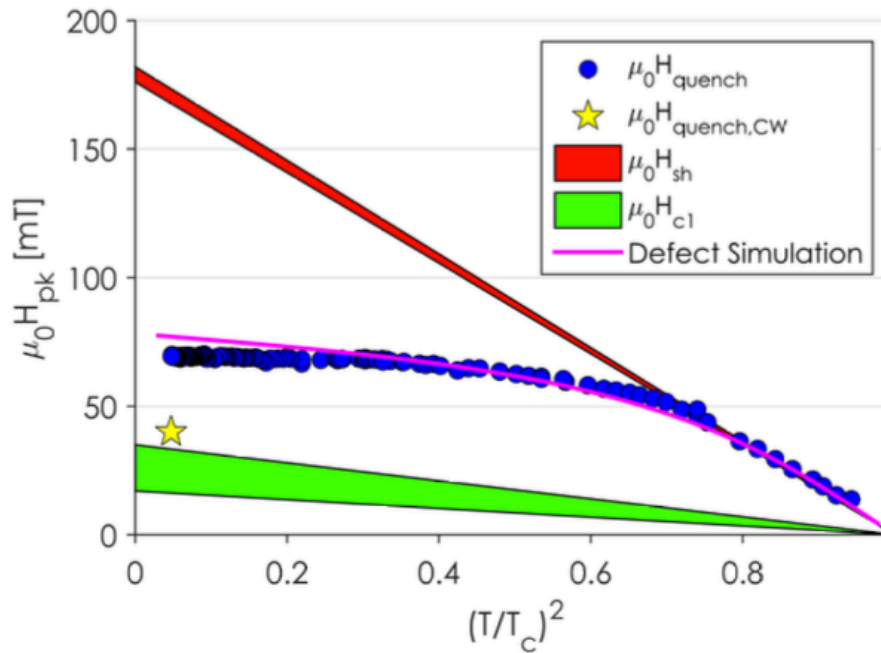
- LTE1-2 N-doped results
 - High T: limited by flux entry at B_{sh}
 - As T decreases, B_{pk} diverges, indicating thermal effects
 - Consistent with thermal model of localized surface defect limitations – either flux entry or thermal runaway
 - Not a fundamental limit!



- LTE1-2 N-doped results
 - B_{pk} vs time to quench:
asymptotically
approaches B_{CW} for
long quench times
 - Again, consistent
with local surface
defects: reaching a
fundamental limit
would be constant
w.r.t. quench time.

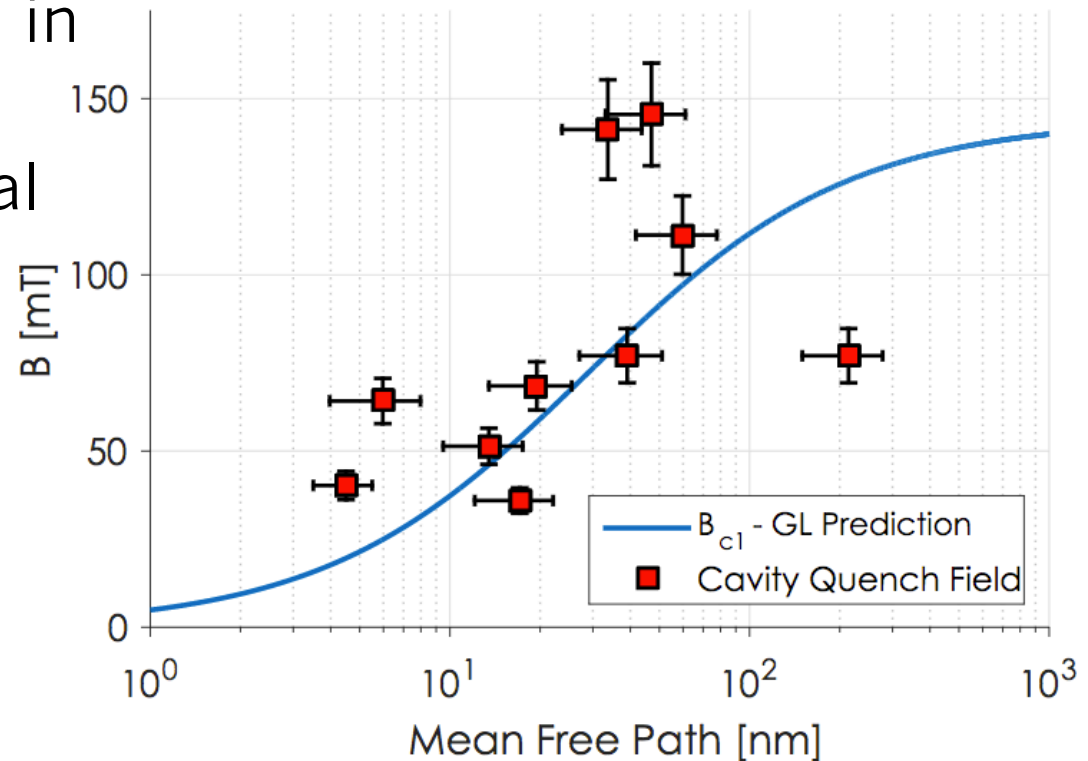


- LTE1-3 N-doped results

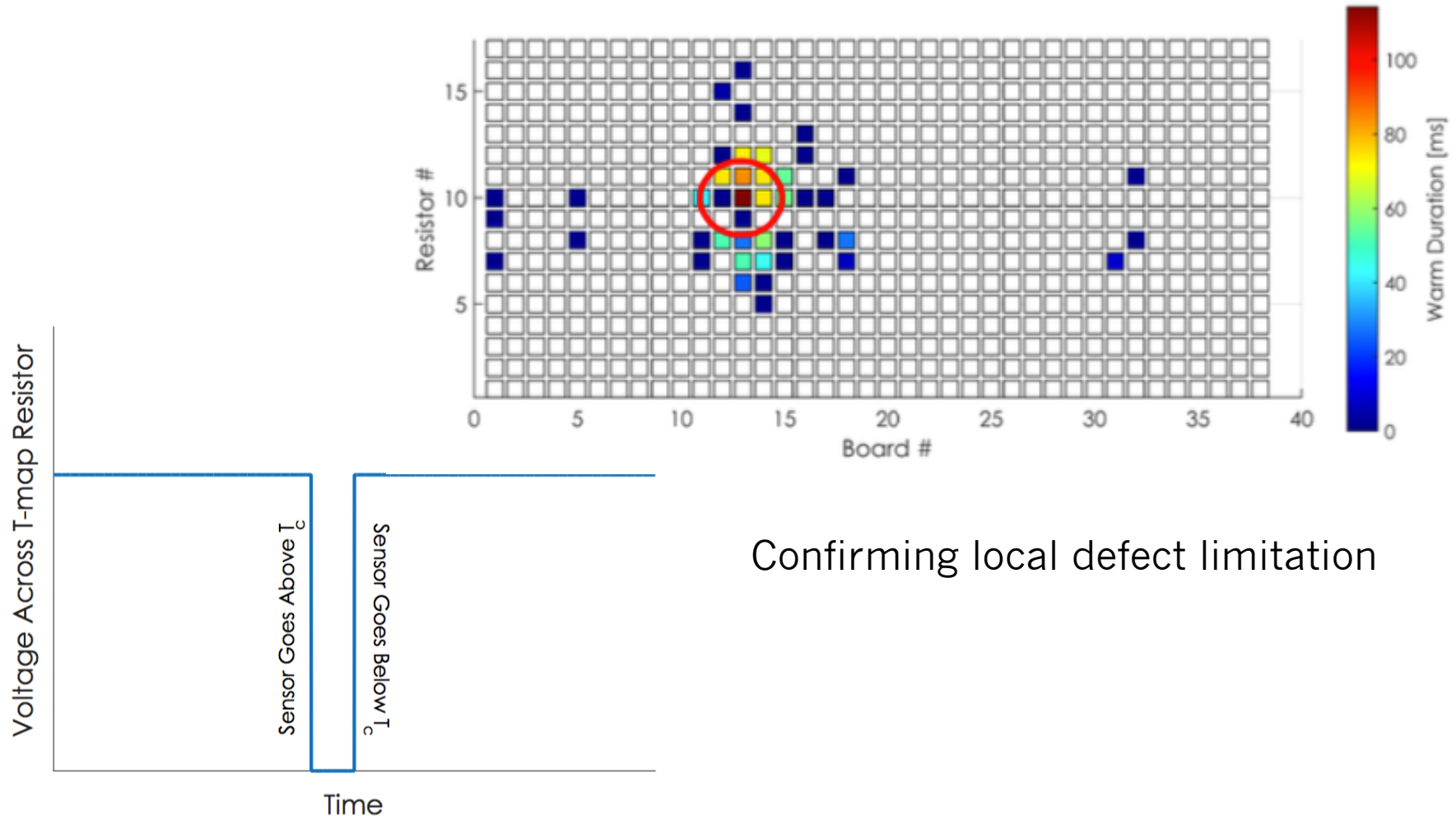


- Qualitatively very similar to LTE1-2, essentially same conclusions: limited by local surface defects, either flux entry or thermal runaway
- Quantitative differences in CW quench field, critical fields, pulsed quench field

- N-doping – exceeding B_{c1}
 - Reached above lower critical field often in CW tests
 - Not a fundamental limit



- N-doping – T-mapping local quench spots



Confirming local defect limitation



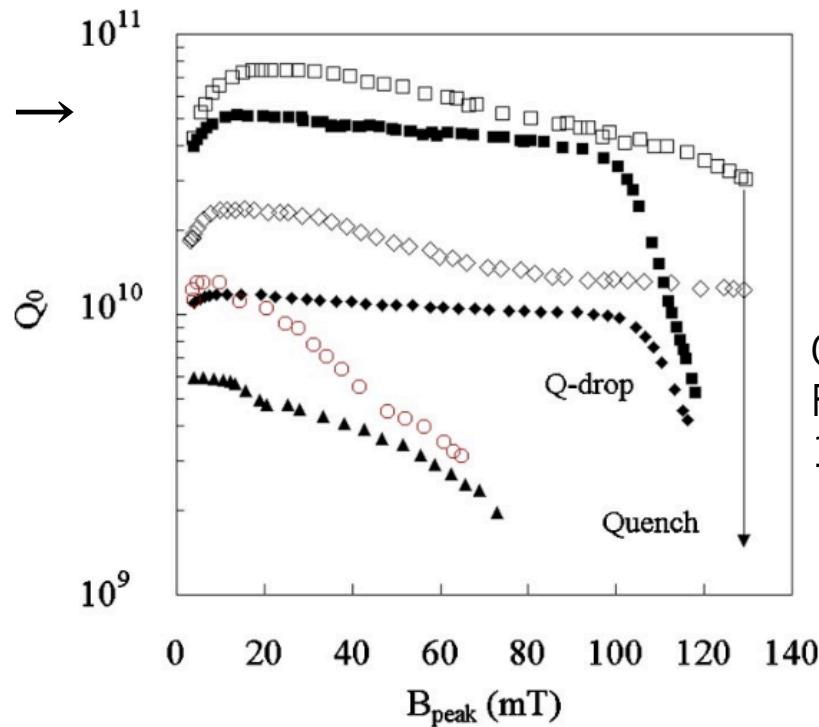
- N-doped results – takeaway:
 - Cavities limited by localized effects on surface defects, either flux entry or thermal runaway
 - B_{sh} is ultimate limit as indicated by high-temperature data
 - Need to mitigate effects of surface defects!
 - We can get above B_{c1} in both pulsed and CW operation



- Klystron testing overview
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- 120°C-baked cavities
 - Compared to standard bulk Nb:
 - Unbaked Nb sees HFQS, largely eliminated in low-T baking. This allows us to reach the fundamental limit of B_{sh} .

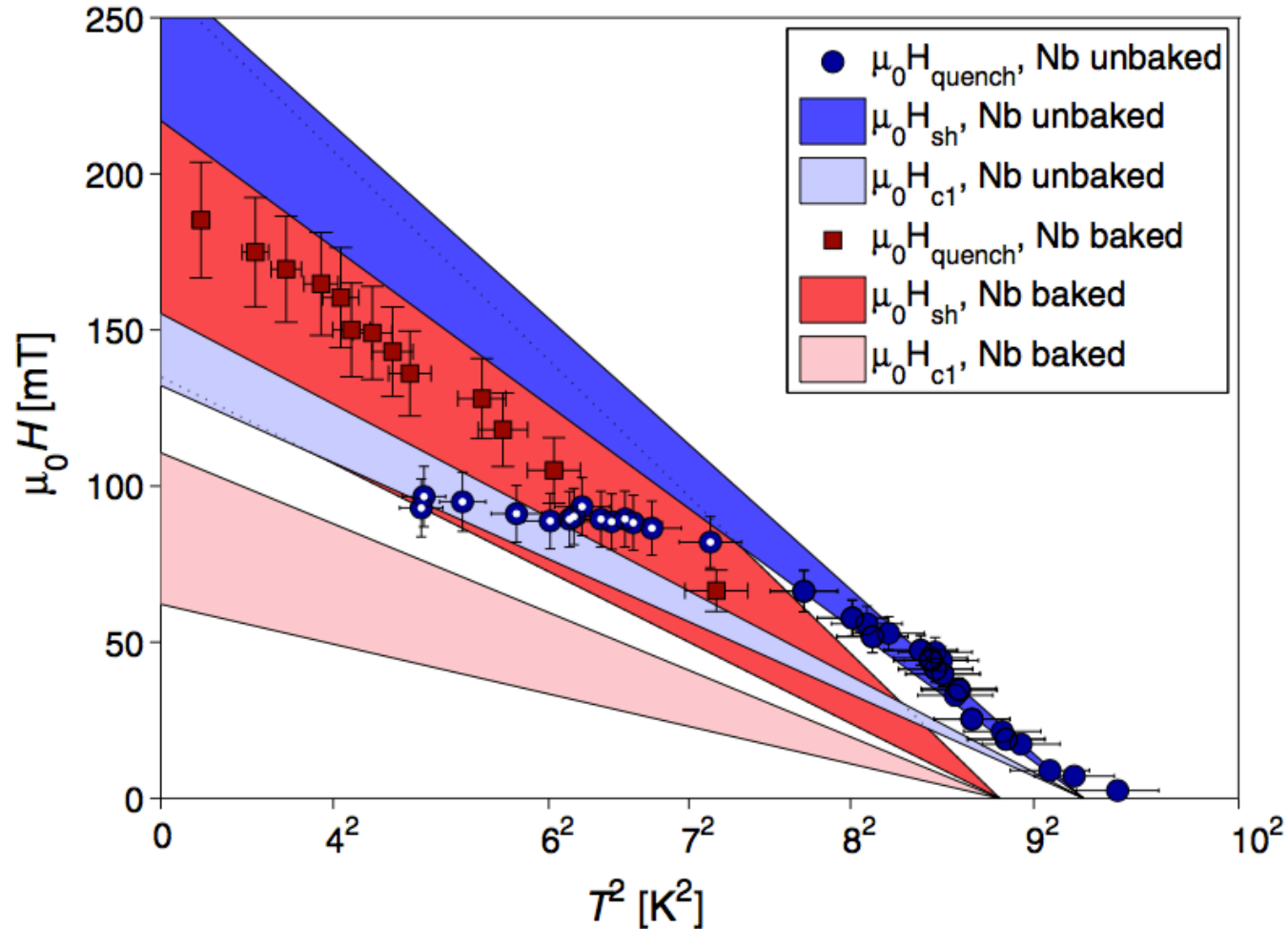
– CW test →



Open points – 120°C bake
 Filled points – unbaked Nb
 1.37 K, 2 K, 2.2 K

G. Ciovati, J. Appl. Phys. 2004

- 120°C-baked cavities





- 120°C-baked cavities – takeaway
 - Reach B_{sh} ! Limit is flux entry quench
 - Eliminate the HFQS/thermal quench of Nb
 - No free lunch – B_{sh} reduced, T_c as well



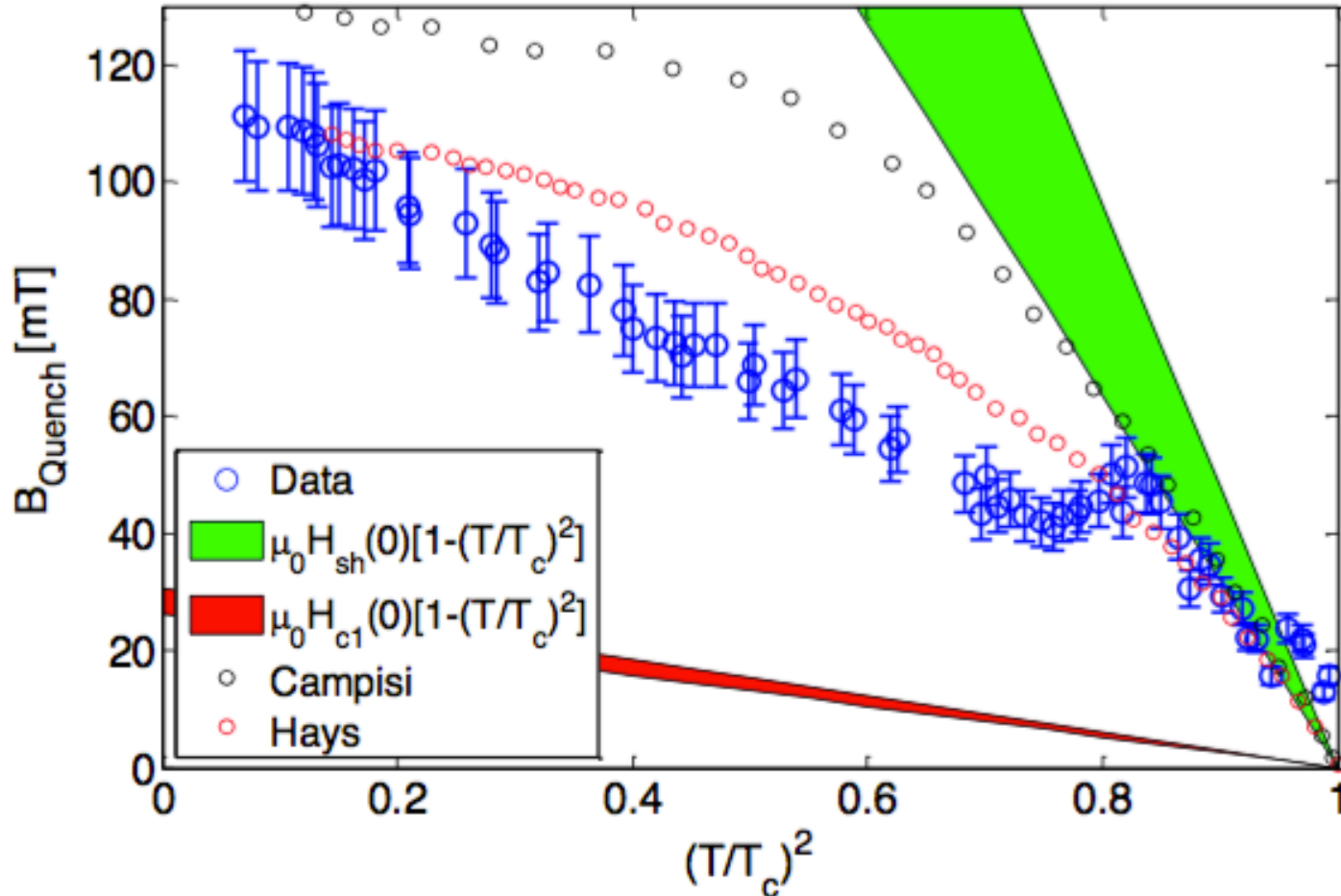
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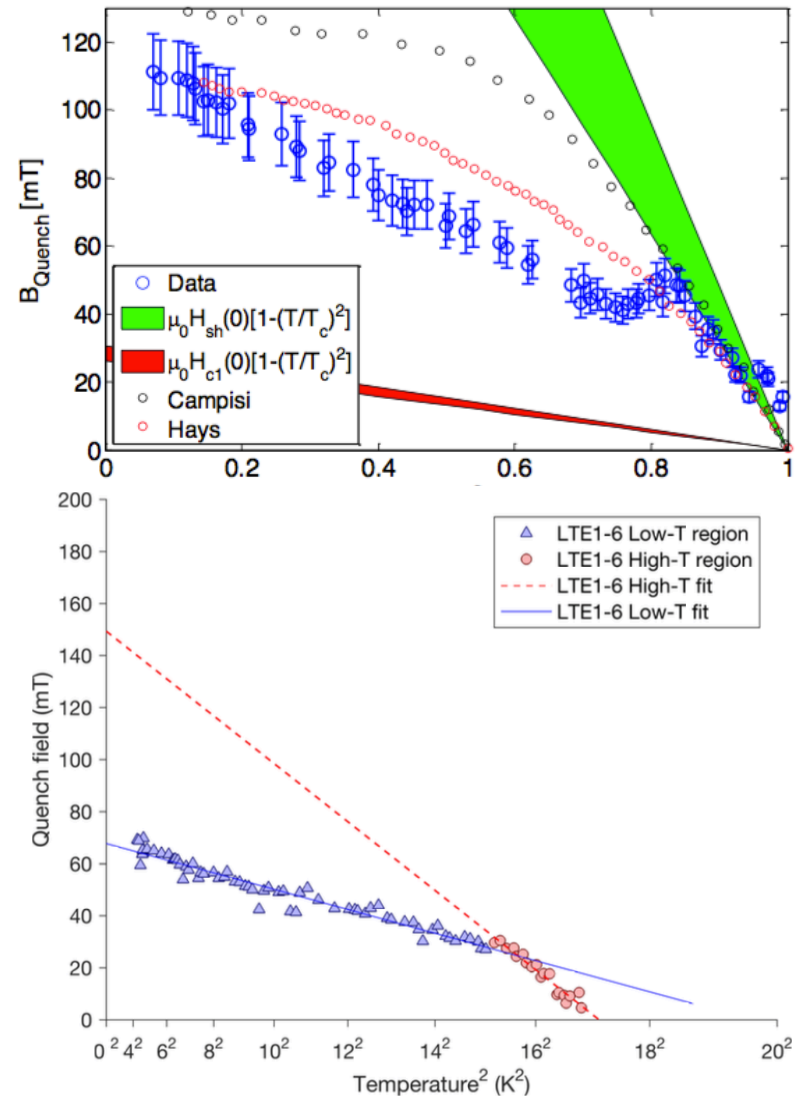
- Nb₃Sn cavities
 - LTE1-6
 - CW quench field: 55 mT (~ 13 MV/m)
 - T_c ~ 17 K
 - ERL1-4
 - CW quench field: 65 mT (~ 15 MV/m)
 - T_c ~ 18 K
 - Older data
 - Campisi and Hays
 - Critical fields:
 - B_{c1} typically ~ 25 mT (strongly type-II)
 - exceeding by far in pulsed and CW tests
 - B_{sh} expected ~ 400 mT



- ERL1-4 + older Nb₃Sn results

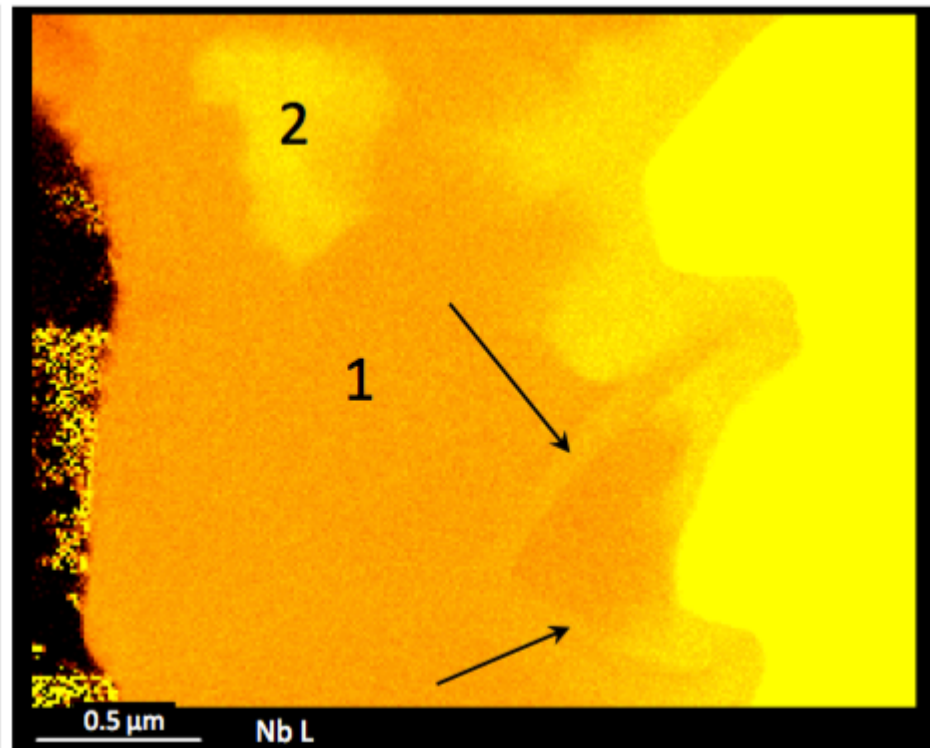
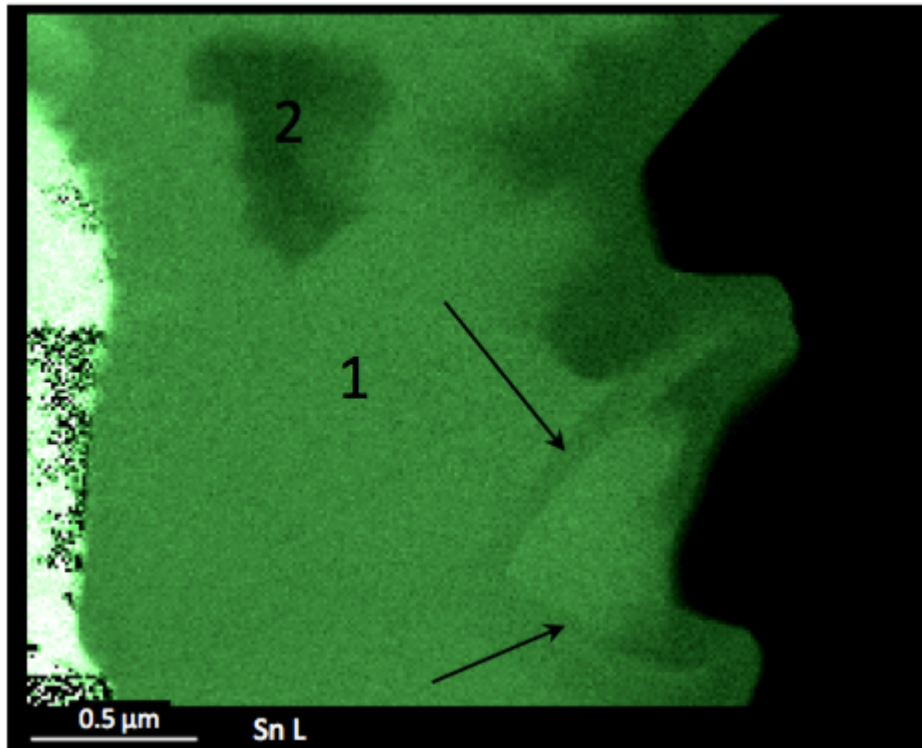


- Nb₃Sn results
 - Bi-regional data indicate two separate regions with distinct limiting critical fields
 - Possibly corresponds with tin-depleted regions or with thin Nb₃Sn regions
 - Lower effective B_{sh} – field enhancement due to surface roughness?
 - Current R&D addressing these issues



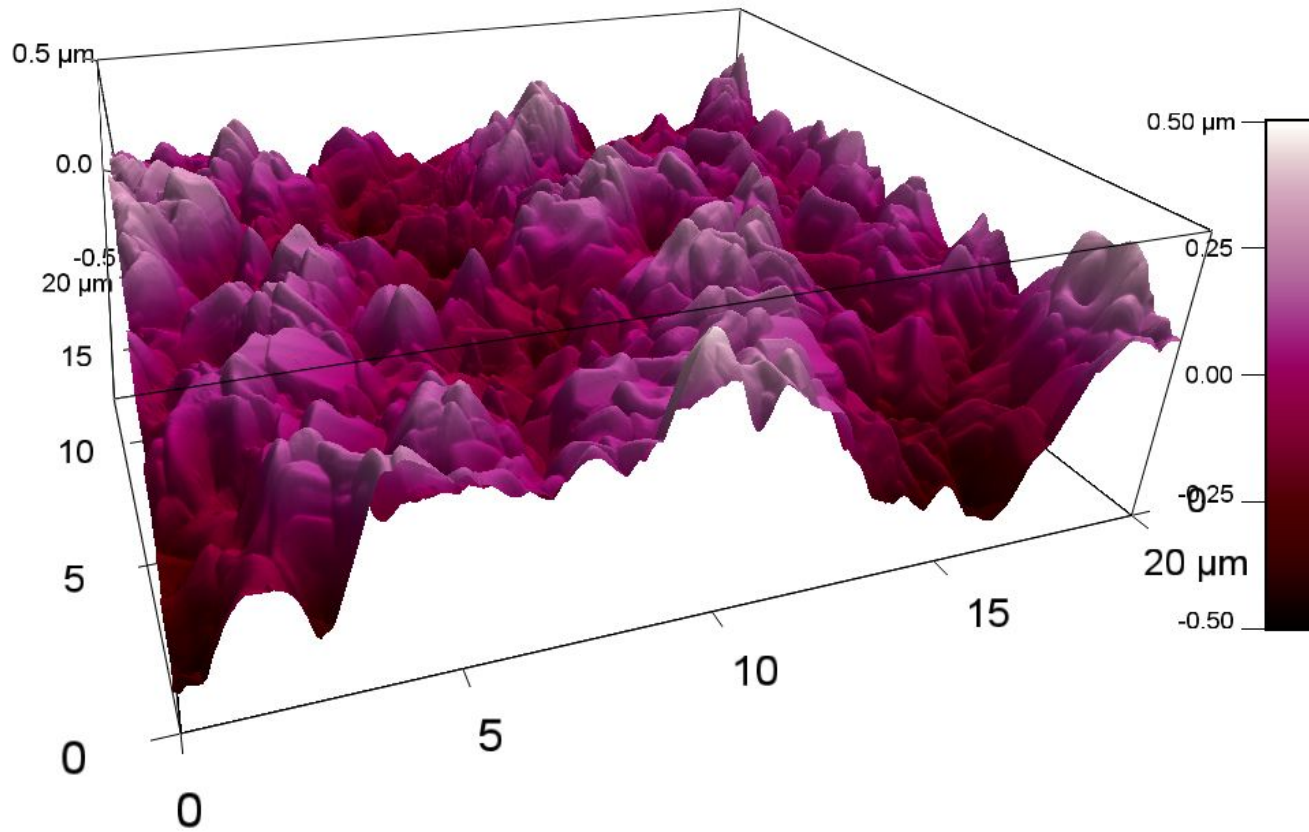
- Nb_3Sn results
 - Tin-depleted regions

Data from T. Proslie, ANL



Area 1: 24 at.% Sn; Area 2: 16 at.% Sn

- Nb_3Sn results
 - Surface roughness \rightarrow field enhancement





- Nb₃Sn results – takeaway:
 - Cavities limited by localized effects on bad regions (thin or tin-depleted), either flux entry or thermal runaway.
 - Ultimate limit B_{sh} effectively lowered due to field enhancement from surface roughness
 - Highly exceeding B_{c1} in CW and pulsed tests



- Concluding thoughts:
 - Ultimate gradient limit is B_{sh}
 - N-doped cavities limited by surface defects
 - Nb_3Sn limited by thin and tin-depleted areas
 - 120°C baked cavities show how we might expect other materials to perform if we can get to B_{sh} .
 - In a perfect world... limiting gradients from B_{sh} :
 - 120°C bake: 200 mT \rightarrow 47 MV/m
 - N-doped: 170 mT \rightarrow 40 MV/m
 - Nb_3Sn : 400 mT \rightarrow 100 MV/m!
 - With surface roughness: \sim 300 mT \rightarrow 75 MV/m



Thank you for your attention!

- References / further reading:
 - S. Posen, N. Valles, and M. Liepe, Phys. Rev. Lett. 115, 047001 (2015).
 - IPAC 2016 papers from J.T. Maniscalco, D. Gonnella, and D.L. Hall

- Backup slide – critical fields

